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ABSTRACT

PROCESS FOR FORMING DEPOSITED FILM BY USE OF ALKYL ALUMINUM HYDRIDE AND PROCESS FOR PREPARING SEMICONDUCTOR DEVICE

In forming a deposited film composed mainly of Al according to the CVD method utilizing gas of alkyl aluminum hydride, hydrogen gas, and if desired, further gas containing Si atoms, film formation is carried out by shifting the deposition rate from a low deposition rate to a high deposition rate.

According to this method, excellent selectivity is exhibited and also a film excellent in flatness can be deposited at a high deposition rate.

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